



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	90mΩ @ V _{GS} = 4.5V	2.8A
20V	120mΩ @ V _{GS} = 2.5V	2.4A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**
- Motor Control

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

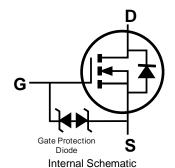
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

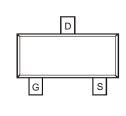






Top View





Top View

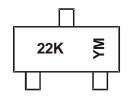
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2302UK-7	SOT23	3,000/Tape & Reel
DMG2302UK-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



22K = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	I _D	2.8 2.2	А	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	I _S	1.1	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I _{DM}	12	Α

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_{D}	0.66	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	192	°C/W
Total Power Dissipation (Note 6)		P_{D}	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	115	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

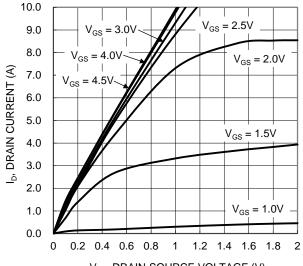
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•		•
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	10	μA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	0.6	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance			61	90	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$
Static Drain-Source On-Resistance	R _{DS(ON)}		80	120	11122	$V_{GS} = 2.5V, I_D = 3.1A$
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance		-	130	_	pF	\/ 40\/ \/ 0\/
Output Capacitance	Coss	l	26	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}	l	18	_	pF	1 – 1.01/11/12
Gate Resistance	R _G	l	2.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}		1.4	_	nC	
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	2.8	_	nC	V 40V L 2.CA
Gate-Source Charge	Q _{GS}		0.1	_	nC	$V_{DS} = 10V, I_D = 3.6A$
Gate-Drain Charge	Q_{GD}	_	0.5	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	0.6	_	ns	
Turn-On Rise Time	t _R	_	2.7	_	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	4.2	_	ns	$R_G = 1\Omega$, $R_L = 2.78\Omega$
Turn-Off Fall Time	t _F	_	1.7	_	ns	
Reverse Recovery Time	t _{RR}		5.3	_	ns	$I_F = 3.6A$, $di/dt = 100A/\mu s$
Reverse Recovery Charge	Q _{RR}		0.5	_	nC	$I_F = 3.6A$, $di/dt = 100A/\mu s$

^{5.} Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.





 $V_{\rm DS}$, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic

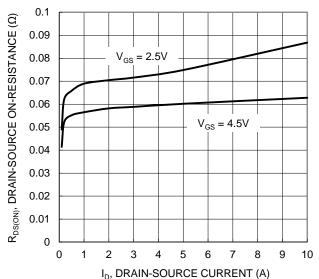


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

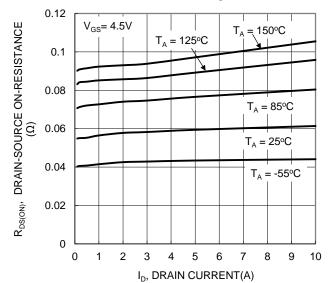
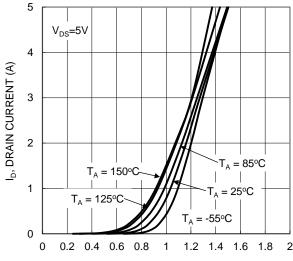
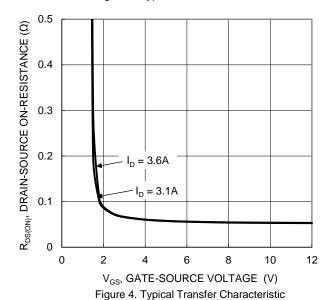


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature



 V_{GS} , GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



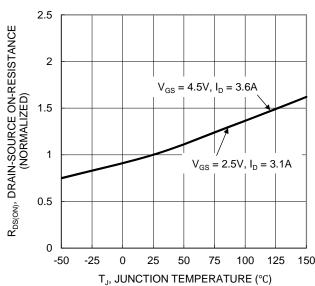


Figure 6. On-Resistance Variation with Junction Temperature



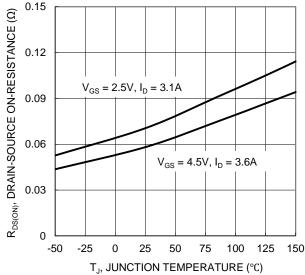


Figure 7. On-Resistance Variation with Junction Temperature

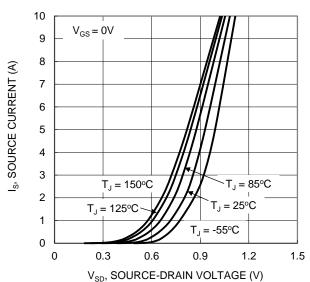


Figure 9. Diode Forward Voltage vs. Current

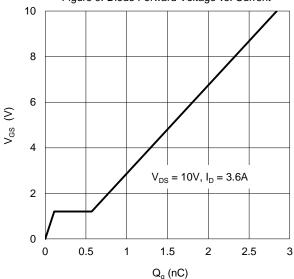


Figure 11. Gate Charge

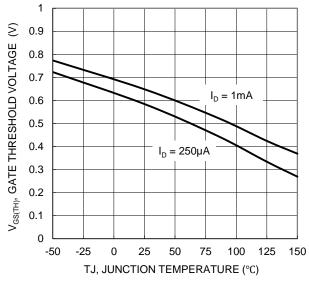


Figure 8. Gate Threshold Variation vs Junction Temperature

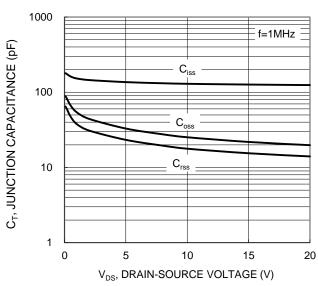


Figure 10. Typical Junction Capacitance

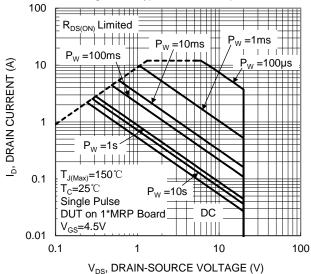


Figure 12. SOA, Safe Operation Area



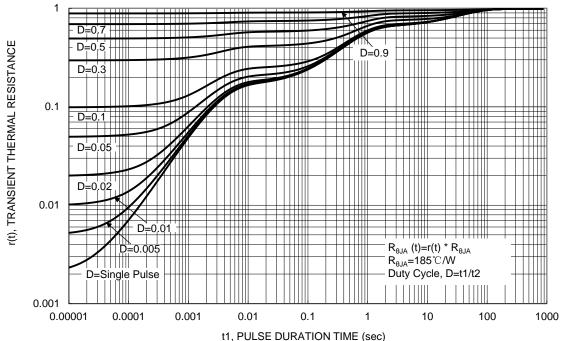


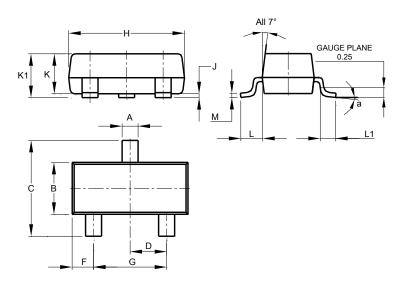
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23

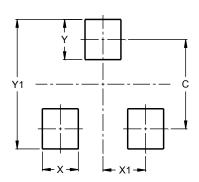


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°	_				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
Y1	2.9				



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